Investigation of the Pulse Operation Wavelength Characteristics of Infrared Emitting Diodes

1976

Anton G. Kuhn
University of Central Florida

Find similar works at: http://stars.library.ucf.edu/rtd

University of Central Florida Libraries http://library.ucf.edu

Part of the Engineering Commons

STARS Citation

http://stars.library.ucf.edu/rtd/229

This Masters Thesis (Open Access) is brought to you for free and open access by STARS. It has been accepted for inclusion in Retrospective Theses and Dissertations by an authorized administrator of STARS. For more information, please contact lee.dotson@ucf.edu.
INVESTIGATION OF THE PULSE OPERATION WAVELENGTH CHARACTERISTICS OF INFRARED EMITTING DIODES

BY

ANTON G. KUHN
B.E.E., Pratt Institute, 1963

RESEARCH REPORT

Submitted in partial fulfillment of the requirements for the degree of Master of Science in Engineering in the Graduate Studies Program of Florida Technological University

Orlando, Florida
1976
ACKNOWLEDGMENT

The author expresses sincere thanks to his wife, Jo Ann, and children, Patricia and John, for their help and understanding during this research effort. He also wishes to thank his advisor, Dr. Ronald L. Phillips, for his excellent advice, encouragement and helpful criticism.
# TABLE OF CONTENTS

Chapter 1 - Introduction

1.1 Objectives 2
1.2 Procedures 2

Chapter 2 - Semiconductor Light Emission 3

2.1 General Information 3
2.2 Light and Infrared Emitting Diodes 4
2.3 Semiconductor Lasers 7

Chapter 3 - Infrared Emitting Diode Wavelength Characteristics 11

3.1 General Information 11
3.2 Thermal Resistance 12
3.3 Transient Thermal Resistance 17
3.4 Use of Transient Thermal Resistance for Infrared Emitting Diodes 21
3.5 Pulse Mode Operation of Infrared Emitting Diodes 23

Chapter 4 - Wavelength Measurement Technique 25

4.1 General Information 25
4.2 Wavelength Measurement Instrument 25
4.3 Input Optical System 27
Chapter 5 - Experimental Measurements

5.1 General Information

5.2 Transient Thermal Resistance Measurements

5.3 Wavelength Measurements

Chapter 6 - Conclusion

6.1 Discussion

6.2 Application of Research Effort

6.3 Recommendations

List of References
CHAPTER 1

INTRODUCTION

1.1 Objectives

The primary objective of this report is to present the findings of the investigation of the pulse operation wavelength characteristics of infrared emitting diodes at room temperature. The area of interest is the change in peak emission wavelength caused by the temperature rise of the diode junction during the application of a current pulse. Major emphasis will be placed on the use of transient thermal resistance of an infrared emitting diode to enable the prediction of emission wavelength change. The secondary objective is to present information in the area of semiconductor light emission.

1.2 Procedures

The first step is to investigate literature to obtain background information in the area of semiconductor light emission. General information in this area will be presented in Chapter 2.

The next step is to identify the characteristics of infrared emitting diodes which describe or influence the change of peak emission wavelength. Chapter 3 will present information in this area.
Having defined the baseline of infrared emitting diodes as related to wavelength shift, the next appropriate step is to establish a wavelength measurement technique to allow for the determination of wavelength change of pulse operated infrared emitting diodes. This information will be presented in Chapter 4.

Having established a wavelength measurement technique, the next step is to measure values of transient thermal resistance for an infrared emitting diode and compare predicted values of peak emission wavelength against measured values. This information will be presented in Chapter 5.

Finally, the conclusion of the research effort will be presented in Chapter 6.
CHAPTER 2

SEMICONDUCTOR LIGHT EMISSION

2.1 General Information

The history of semiconductor light emission goes back to the early 1900's. Mims (1) relates that an electrical engineer named Henry J. Round, in 1907, touched two wires connected to a battery across a crystal of silicon carbide and observed that the crystal emitted yellowish light. Although Round may not have realized it at the time, he had operated the first crude light emitting diode. A period of 55 years followed when in 1962, as presented by Gooch (2), Hall and co-workers at the General Electric Research Laboratories in Schenectady, New York, succeeded in making the first semiconductor laser which followed the ruby laser in 1960 and the gas laser in 1961.

The above mentioned semiconductor light emission sources, namely, light emitting diodes and semiconductor lasers, are similar in that their operation is based on an electrical current being passed through a p-n junction. The major difference is that the light emitting diode is an incoherent radiation source while the semiconductor laser, as the name implies, is a coherent radiation
source. Besides the p-n junction semiconductor laser, there are other types of semiconductor lasers, such as those presented by Sze (3), which employ optical, electron beam and avalanche breakdown methods to achieve laser action.

The infrared emitting diode, whose pulse operation wavelength characteristics are the subject of this report, followed the light emitting diode in development and is identical in operation with the exception that the radiated emission is in the infrared portion of the spectrum.

Information regarding the physics of light and infrared emitting diodes and semiconductor lasers is readily available and therefore will not be presented in this report except when relevant to the research effort.

2.2 Light and Infrared Emitting Diodes

The light emitting diode (sometimes referred to as luminescent diode) and the infrared emitting diode are much simpler than the semiconductor laser. They are semiconductor diodes which emit visible and infrared energy when forward biased.

There are many types of structural configurations for light and infrared emitting diodes. Configurations include flat, mesa, dome and optical fiber emitter designs. Two flat emitter configurations are illustrated in Figure 1. The n-type material is selected to be
relatively transparent at the emission wavelength.

(a) Planar surface emitter  (b) Edge emitter

Fig. 1 Light and infrared emitting diode flat configurations

A typical curve for output power as a function of forward current is shown in Figure 2 for the continuous operation of light and infrared emitting diodes. The radiation starts at low values of forward current and increases nearly linearly until the output decreases due to overheating or saturation of the light-emitting process.

Fig. 2 Radiant flux versus forward current for typical light and infrared emitting diodes
The light and infrared emitting diodes may also be operated in the pulse mode. Additional information in this area will be presented in Chapter 3.

The wavelength of photon emission, $\lambda$, is given as

$$\lambda = \frac{hc}{E} \quad (2.1)$$

where

- $h = 6.624 \times 10^{-34}$ joule-seconds
- $c = 3 \times 10^8$ meters per second
- $E =$ energy in joules that separates the valence and conduction bands in the semiconductor diode

By expressing the denominator of the above equation as $E_g$, the bandgap separation in electron-volts, we obtain the following

$$\lambda = \frac{1240 \text{ nanometers}}{E_g} \quad (2.2)$$

A well defined bandgap will produce essentially monochromatic radiation. However, the light and infrared emitting diodes have spectral bandwidths (spectral line width between half-intensity points) of typically 25 to 50 nanometers. The wide variation is due to variations in the bandgap and transition levels therein.

By using semiconductors with different bandgaps, it is possible to obtain radiated emission from the blue portion of the visible spectrum to more than 30 micrometers.
2.3 Semiconductor Lasers

As previously mentioned, there are many types of semiconductor lasers. However, this section will be devoted to one, namely, the injection laser (sometimes called the p-n junction laser), because of its commercial availability and its similarity to light and infrared emitting diodes in being a current dependent diode radiation source.

The basic configuration of the injection laser is illustrated in Figure 3. It is noted that the presented configuration is similar to the flat edge emitter configuration shown for light and infrared emitting diodes. A pair of parallel planes are polished or cleaved perpendicular to the plane of the p-n junction. The two remaining sides of the diode have roughened surfaces to
eliminate lasing in directions other than the main one. This type of structure is called a Fabry-Perot cavity.

The injection laser operates similarly to an incoherent emitting diode when operated at low forward currents. However, as shown in Figure 4, if the forward current exceeds a threshold, lasing occurs and there is a major change in the slope of the output power versus forward current curve. Unlike the light and infrared emitting diodes at room temperature, the p-n junction laser cannot be operated in the continuous mode. This is because of the high current densities required to produce lasing. As reported by RCA Corporation (4), a typical threshold current is 10 amperes with a peak forward current being 40 amperes. The current density to produce lasing can be 10,000 to 20,000 amperes per square
centimeter with the operating current density being typically 50,000 amperes per square centimeter.

Sustained application of these high current densities would cause a very rapid rise in junction temperature, quenching of the lasing action and eventual destruction of the diode. Therefore, p-n junction lasers must be operated only in the pulse mode and within the specified maximum pulse duration and duty cycle. Typical values for p-n junction laser maximum pulse duration and duty factor are 2 microseconds and 0.1 percent respectively.

The p-n junction laser mentioned above is referred to as a homostructure injection laser because it is made of a single material such as gallium arsenide. The n and p regions are formed by the addition of dopants. An advancement of the p-n junction laser is the heterostructure injection laser which has enabled continuous wave laser operation at room temperature. The basic principle of the heterostructure injection laser is the use of gallium aluminum arsenide in the case of a gallium arsenide laser to form an optical waveguide based on the difference in the index of refraction for each material to contain the light emission in the active region. The result is a decrease in the threshold current sufficient to allow operation at room temperature in the continuous mode.

Similar to the light and infrared emitting diode, the emitted radiation of the injection laser is generated
by a process of recombination. The emission wavelength is determined by the bandgap and the doping of the semiconductor.

The spectral bandwidth of an injection laser is typically 3.5 nanometers which is approximately one-tenth that of light and infrared emitting diodes.
CHAPTER 3

INFRARED EMITTING DIODE

WAVELENGTH CHARACTERISTICS

3.1 General Information

As previously stated, the area of interest of this report is the change in peak emission wavelength caused by the temperature rise of the diode junction during the application of a current pulse. Because of the common use of gallium arsenide for infrared emitting diodes, this report will limit discussion to that type material.

The peak emission wavelength data as given for gallium arsenide infrared emitting diodes by manufacturers is based on steady state conditions. Table 3-1 presents emission wavelength data for some common infrared emitting diodes.

Table 3-1. Emission Wavelength Data

<table>
<thead>
<tr>
<th>Manufacturer</th>
<th>Type</th>
<th>Peak Wavelength</th>
<th>Forward Current</th>
<th>Temperature</th>
</tr>
</thead>
<tbody>
<tr>
<td>Texas Instruments</td>
<td>TIXL27</td>
<td>940 nm</td>
<td>300 mA</td>
<td>25°C-stud</td>
</tr>
<tr>
<td>Texas Instruments</td>
<td>TIL26</td>
<td>930 nm</td>
<td>35 mA</td>
<td>25°C-air</td>
</tr>
<tr>
<td>Spectronics</td>
<td>SE3453</td>
<td>940 nm</td>
<td>100 mA</td>
<td>25°C-case</td>
</tr>
<tr>
<td>General Electric</td>
<td>LED56</td>
<td>940 nm</td>
<td>100 mA</td>
<td>25°C-case</td>
</tr>
<tr>
<td>RCA</td>
<td>SG1004</td>
<td>940 nm</td>
<td>50 mA</td>
<td>27°C-case</td>
</tr>
</tbody>
</table>
As seen from the table, the value of peak emission wavelength is based on maintaining a reference temperature constant for a stated value of forward current. Stud temperature is associated with power type infrared emitting diodes while case temperature is associated with metal case devices. The stud and case type devices are usually mounted on appropriate heat sinks with the stud and case acting as the interface for removal of heat from the diode junction. Air temperature is the reference for plastic enclosed diodes. The importance of this reference temperature is that the wavelength of peak emission, for the specified forward current, varies directly with the change in reference temperature. Typical values of change in wavelength of peak emission versus reference temperature as found on manufacturer data sheets vary between 0.27 and 0.30 nanometers per °C. Additional consideration of this factor will be presented later in this report.

More important is the establishment of a baseline to describe the junction thermal behavior of an infrared emitting diode. The appropriate candidate is the thermal resistance of the diode. This is because the value of thermal resistance relates change of the junction temperature to the input power to the device.

3.2 Thermal Resistance

Thermal resistance is the ratio of temperature rise to the rate at which heat is generated within a device.
under steady state conditions. It is noted that some reference material uses the term thermal impedance in place of thermal resistance. The normal units for thermal resistance are °C/W.

As presented by Texas Instruments Incorporated (5), the thermal resistance of an infrared emitting diode is a difficult parameter to calculate accurately but one which can be measured with a reasonable degree of accuracy. The junction temperature can be approximated by

\[ T_J = P_D \Theta_{JR} + T_R \]  

(3.1)

where

- \( T_J \) = junction temperature
- \( P_D \) = input power (forward current times forward voltage)
- \( \Theta_{JR} \) = junction to temperature reference thermal resistance
- \( T_R \) = temperature of reference point

The method used to measure the thermal resistance of a diode is based on the fact that the voltage across a p-n type junction at a fixed forward current varies inversely and almost linearly with the junction temperature. The first step in the measurement process is to calibrate the diode in an oven at a constant forward current. The calibration current is small compared to the maximum allowable forward current specified for continuous direct current operation. The result is a curve of forward
voltage versus junction temperature for the diode which will be used as a calibration standard. It is important that the preceding voltage measurement be made after the junction temperature has reached steady state temperature in order to minimize measurement error. The next step is to place the diode on a constant temperature heat sink in the case of stud and case type devices and in a constant temperature air environment in the case of plastic enclosed diodes. Test circuitry capable of interrupting forward direct current through the diode for periods of 100 microseconds at about a one-percent duty cycle is used as the basis for providing the additional information necessary for determining the thermal resistance of the diode. During the 100 microsecond period, the calibration current used in the first step is applied to the diode and the forward voltage is measured for different values of forward current. As before, the voltage measurement must be made after the junction temperature reaches the steady state value. The junction temperature corresponding to measured values of forward voltage is read from the previously obtained forward voltage versus junction temperature curve. In this manner, a plot of junction temperature versus input power may be obtained by taking power and forward voltage readings for several values of forward current. The slope of the obtained curve is the thermal resistance of the infrared emitting diode.
The thermal resistance of stud and case type infrared emitting diodes is usually specified as $\theta_{JC}$ which represents the steady state rise in junction temperature with respect to the case (stud) per watt of applied input power. This is because these type devices are usually operated when mounted on a heat sink. The thermal resistance of plastic enclosed infrared emitting diodes is specified as $\theta_{JA}$ since ambient air temperature is used as the reference for determining the temperature rise of the diode junction. In some instances, manufacturers also give the value of $\theta_{JA}$ for metal case diodes. This allows for the determination of maximum operating characteristics when a heat sink is not used for the diode cooling but instead ambient air. Typical values of thermal resistance, $\theta_{JC}$, are on the order of 10 to 20 °C/W for power type infrared emitting diodes and 50 to 100 °C/W for metal case types. Typical values of $\theta_{JA}$ for plastic enclosed diodes range between 200 and 300 °C/W.

The use of the thermal resistance value for a device is best illustrated by an example. Suppose we have a device with maximum ratings as follows:

<table>
<thead>
<tr>
<th>Junction temperature</th>
<th>100 °C</th>
</tr>
</thead>
<tbody>
<tr>
<td>Thermal resistance (junction-case)</td>
<td>20 °C/W</td>
</tr>
<tr>
<td>Thermal resistance (junction-air)</td>
<td>120 °C/W</td>
</tr>
</tbody>
</table>

The first area of concern will be to determine the junction temperature when the device is operated without
a heat sink in an ambient temperature of 40 °C and with an input power of 150 milliwatts. In this case we can use equation 3.1 which results in

\[ T = 0.150 \text{ W} \times 120 \degree \text{C/W} + 40 \degree \text{C} \]

\[ = 58 \degree \text{C} \]

The second part of the example will be to determine the rating (°C/W) of the heat sink required to maintain the junction temperature below the maximum rating when the input power is 3 watts (assumed to be within the device safe area of operation) and the ambient temperature is 25 °C. Again, we use equation 3.1 and the fact that the thermal resistance, \( \theta_{TR} \), is equal to the sum of \( \theta_{JC} \) and \( \theta_{HS} \), the thermal resistance of the heat sink. Solving for \( \theta_{HS} \), we obtain

\[ \theta_{HS} = \frac{(T_J - T_A)}{P_D} - \theta_{JC} \]

\[ = \frac{(100 \degree \text{C} - 25 \degree \text{C})}{3 \text{ W}} - 20 \degree \text{C/W} \]

\[ = 5 \degree \text{C/W} \]

The above example excluded the thermal resistance of the connection between the case of the device and the heat sink. The value is on the order of 0.5 °C/W and is based on the heat sink having good surface contact with the device and a thermally conductive grease covering the entire contact area. This value becomes significant in many high power device applications, power transistors
in particular, where $\theta_{JC}$ may be on the order of $1 \, ^\circ\text{C/W}$ or less.

The concept of thermal resistance is not applicable to pulse operation of infrared emitting diodes when the pulse length is less than the time necessary for the device to reach thermal equilibrium because the steady state value does not take into account the thermal capacity of the device. An approach which seems promising is to look at the application of transient thermal resistance to describe thermal behavior of infrared emitting diodes.

### 3.3 Transient Thermal Resistance

As presented by Motorola Semiconductor Products Incorporated (6), a time dependent factor $r(t)$ is applied to the steady state thermal resistance value to account for thermal capacity of a device. Thermal resistance, at a given time, is called transient thermal resistance and is given by

$$ \theta_{JR}(t) = r(t) \theta_{JR} \quad (3.2) $$

The transient thermal resistance has been determined to be extremely complex when presented as a mathematical expression. The response is, therefore, plotted from empirical data. The value of $r(t)$ is first determined as a function of pulse width for a duty cycle, $D$, equal to zero where
A duty cycle of zero for a given pulse width implies an infinite pulse repetition period and allows for single pulse analysis. By applying a step function change in input power for a given pulse width, we can measure junction temperature at the end of the pulse in a manner similar to that employed for determining the thermal resistance of a device. We can then use equation 3.1 with $\Theta_{TR}$ replaced by $\Theta_{TR}(t)$ and then solve for the transient thermal resistance. From equation 3.2, we solve for $r(t)$ as follows:

$$r(t) = \frac{\Theta_{JR}(t)}{\Theta_{JR}}$$  \hspace{1cm} (3.4)

The above method is repeated for a number of different pulse widths. The procedure is then repeated for different values of duty cycle. The values of $r(t)$, the normalized transient thermal resistance, are then plotted versus pulse width for the selected values of duty cycle. A typical curve of $r(t)$ versus pulse width for a transistor is shown in Figure 5 for duty cycles of 0, 0.1, and 0.5.

An example best illustrates the use of transient thermal resistance data. Assume we are using a transistor which is represented by the curves contained in Figure 5 operating under the following conditions:

$$D = \frac{\text{Pulse Width (t)}}{\text{Pulse Repetition Period (T)}}$$  \hspace{1cm} (3.3)
Fig. 5 Typical transistor curves of \( r(t) \) versus pulse width for selected duty cycles

Input pulse power \( 5 \text{ W} \)

Pulse duration \( 1 \text{ ms} \)

Pulse repetition period \( 10 \text{ ms} \)

Case temperature (constant) \( 50 ^\circ \text{C} \)

Thermal resistance (junction-case) \( 35 ^\circ \text{C/W} \)

The first part of the example is to find the junction temperature at the end of the first pulse. In this case we can use equation 3.1 with \( \theta_{JC}(t) \) substituted for \( \theta_{JR} \) which results in
\[ T_J = r(1 \text{ ms}) \theta_J \cdot P_D + T_c \]

The term \( r(1 \text{ ms}) \) is read directly from the graph of Figure 5 using the \( D=0 \) curve. Therefore we have

\[ T_J = 0.15 \times 35 \, ^\circ\text{C}/\text{W} \times 5 \, \text{W} + 50 \, ^\circ\text{C} \]
\[ = 76.25 \, ^\circ\text{C} \]

The second part of the example is to find the junction temperature at the end of a pulse under steady state conditions. In this case we see that the duty cycle is 0.1. We therefore obtain the value of \( r(1 \text{ ms}) \) from the \( D=0.1 \) curve which results in

\[ T_J = 0.23 \times 35 \, ^\circ\text{C}/\text{W} \times 5 \, \text{W} + 50 \, ^\circ\text{C} \]
\[ = 90.25 \, ^\circ\text{C} \]

The average junction temperature is given by using the average input power, \( P_D \) times \( D \), in equation 3.1 which gives

\[ T_J^{(AV)} = 35 \, ^\circ\text{C}/\text{W} \times 0.5 \, \text{W} + 50 \, ^\circ\text{C} \]
\[ = 67.5 \, ^\circ\text{C} \]

It is noted that the junction temperature at the end of any power pulse does not equal the sum of the average temperature rise (17.5 \( ^\circ\text{C} \) in this example), the rise due to one pulse (26.25 \( ^\circ\text{C} \) in this example) and the reference temperature because cooling occurs between power pulses.

As seen above, the concept of transient thermal
resistance is a useful tool for analysing the pulse operation behavior of devices. It allows for the use of lower power rated devices for low duty cycle applications.

3.4 Use of Transient Thermal Resistance for Infrared Emitting Diodes

The value of thermal resistance is presently used by manufacturers to describe the steady state behavior of the infrared emitting diode junction temperature. This is made possible by the fact that the radiated power output (which represents a cooling process) is a very small percentage of the input power (typical values range between 0.5 and 2.0 percent) and that the percentage remain fairly constant over the operating range. This is also the case for operating the diode in the pulse mode. Further, any major change in radiation efficiency will produce a very minor change in the power dissipated in the device because of the low efficiency. Therefore, the use of transient thermal resistance is considered a useful technique to describe the behavior of the infrared emitting diode junction temperature.

Since we can use transient thermal resistance to determine the junction temperature of the infrared emitting diode for pulse mode operation, the last remaining area of concern is to describe the variation in peak emission wavelength as a function of junction temperature.
As previously stated, the wavelength of peak emission for an infrared emitting diode, for a fixed forward current, varies directly with reference temperature. For gallium arsenide type light emitting diodes, this variation is linear. The problem is that manufacturers data expresses the change in peak emission wavelength as a function of the stud or case temperature and not the junction temperature. As it turns out, the stated value is slightly lower than the desired value. The actual value of peak emission wavelength change per unit change in junction temperature can be obtained from the characteristics of the diode.

Consider a typical infrared emitting diode with the following stated characteristics:

- **Forward current (continuous)**: 100 ma
- **Thermal resistance (junction-case)**: 75°C/W
- **Wavelength temperature coefficient**: 0.28 nm/°C (case temperature at stated forward current)
- **Forward voltage temperature coefficient**: -1.8 mv/°C (at stated forward current)

Assume that we have a 50 °C change in the case temperature. We see that for the stated forward current the forward voltage drop across the diode decreases by 90 millivolts. This represents a decrease in input power of 9 milliwatts. This implies by use of the stated
thermal resistance value that the temperature difference between the case and junction decreased by 0.675 °C. Therefore, the corresponding rise in junction temperature is 49.325 °C which results in a value of 0.284 nanometers per °C for the value of peak emission wavelength change per unit change in junction temperature.

Based on the above, we see that we can use the manufacturers stated value of peak emission wavelength change per unit change in case or stud temperature for a particular diode as a reasonable approximation to describe the peak emission wavelength change per unit change in junction temperature.

3.5 Pulse Mode Operation of Infrared Emitting Diodes

Before one attempts to operate an infrared emitting diode in the pulse mode, a review of some basic factors is in order.

The maximum peak forward current, $I_{FPM}$, for pulse mode operation can be approximated by

$$I_{FPM} = \frac{I_F}{D}$$

where

$I_F$ = maximum rated continuous forward current

$D$ = duty cycle

As can be seen, if we desire to increase the peak forward current (maximum) while operating the device in
the pulse mode, we must decrease the duty cycle. This implies that we either decrease the pulse width or increase the pulse repetition period or change both parameters to achieve a reduction in duty cycle. The limiting value of maximum peak forward current for pulse operation is usually based on the value of current that will cause bonding wires inside the device to open. This value is specified by manufacturers and is given for a stated pulse width and duty cycle. Typical values are on the order of 5 to 10 amperes.

The approximation of equation 3.5 does not include any consideration of temperature and power dissipation factors. For proper design of a system employing infrared emitting diodes, these factors are very important and should be considered as well as trade-offs such as duty cycle, pulse repetition period and peak current. The manufacturers data sheet should be used as a basis for design with particular attention given to the absolute maximum ratings for the infrared emitting diode.
CHAPTER 4

WAVELENGTH MEASUREMENT TECHNIQUE

4.1 General Information

A sound wavelength measurement technique is essential to allow for the determination of wavelength changes associated with pulse operated infrared emitting diodes. Some important factors to be considered are the type of instrument to be used for the wavelength measurement, the input optical system to be used to match the source to the wavelength measurement instrument and the technique used to measure the wavelength measurement instrument output.

4.2 Wavelength Measurement Instrument

The wavelength measurement instrument available to measure the peak emission wavelength change of infrared emitting diodes is the Hilger-Engis Model 1000 Monochromator Spectrometer. The unit is a plane grating, symmetrical Czerny-Turner spectrometer in which radiation transmitted through the entrance slit is collimated and directed toward the diffraction grating by a collimating mirror. The diffraction grating disperses the incident radiation and part of the dispersed radiation falls onto a focusing mirror which directs and focuses the spectrum to
and at the exit slit. The layout of the Czerny-Turner spectrometer is illustrated in Figure 6. The focal length for both the collimating and focusing mirror is one meter.

For changing the wavelength band passing through the exit slit, the diffraction grating is rotated either by a manual drive or by a motor drive. The wavelength of the outgoing radiation is indicated by a mechanical counter, directly in angstroms. By changing diffraction gratings, the spectrometer can be used over the wavelength range of 185 nanometers to 30 micrometers.
The instrument will be used with a one micrometer diffraction grating (first order blaze wavelength) which provides high efficiency in the radiation spectrum of gallium arsenide infrared emitting diodes.

4.3 Input Optical System

Davis (7) discusses the importance of input slit illumination since the illumination of the slit and the slit width determine how much radiated energy enters the spectrometer and produces a useful diffraction pattern. The solid angle of radiated energy, $\Omega$, accepted by the spectrometer is determined by the size of the diffraction grating and the focal length of the collimating mirror. This solid angle must be geometrically filled with radiated energy from the source, at the very least, in order to utilize the instrument properly. If an image of the source is focused on the slit, the solid angle of radiated energy from the input lens system, $\Omega_{LS}$, must be at least as large as the solid angle of the spectrometer, as shown in Figure 7.

A typical optical design for the input optical system is best illustrated by an example. Suppose we have a source which radiates into a solid angle of 0.04 'r steradians and desire to design an input optical system using 40 millimeter diameter lenses which properly illuminates the input slit of the spectrometer. An input optical system design to achieve the stated objectives is
Fig. 7 Illumination of spectrometer

illustrated in Figure 8 where $f_{cl}$ is equal to the focal length of the collimating lens and the distance between the lens and the source, $f_{fl}$ is equal to the focal length of the focusing lens and the distance between the lens and input slit, $d$ is equal to the lens diameter and $l$ is equal to the separation between the lenses.

Fig. 8 Input optical system design
The first step will be to calculate the value of $f_{cl}$. We can make use of the fact that solid angle is defined as the surface area at a given radius divided by the square of the radius. This results in

$$\Omega = \pi (d/2)^2 / f_{cl}^2$$  \hspace{1cm} (4.1)

Solving for $f_{cl}$, we obtain

$$= \sqrt{\pi/\Omega} \text{ d}/2$$
$$= \sqrt{\pi/0.04 \pi} \text{ 4}/2 \text{ cm}$$
$$= 10 \text{ cm}$$

The next step is to calculate the value of $f_{fl}$. Here we make use of the fact that the f/number of the spectrometer must equal the f/number of the focusing lens. The latter is given by

$$\text{f/number} = f_{fl} / d$$  \hspace{1cm} (4.2)

The f/number for the spectrometer is found to be 10 from the manufacturers data for a measurement wavelength of 940 nanometers. Solving equation 4.2 for $f_{fl}$ gives

$$f_{fl} = 10 \text{ d}$$
$$= 40 \text{ cm}$$

The value of $d$ is not critical but should be kept small in order to minimize design problems.

It is pointed out that this same design concept is
applicable to the output of the spectrometer. A collimating lens can be used to collimate the diverging output of the spectrometer while a second focusing lens can provide for imaging of the slit onto a sample (useful for absorption spectroscopy).

The input slit width to be used depends on the method of slit illumination, the fraction of theoretical resolution desired and the required throughput. These factors must be carefully considered in order to provide the basis required for wavelength measurement.

While not a problem for our application since we have a single wavelength source, a problem sometimes occurs when the spectrometer is used to measure specific wavelengths of a source with a wide spectral range. The result is an overlapping of orders which occurs when different wavelengths appear at the same angle but in different orders. For example, if a spectrum at 750 nanometers is to be observed in the first order, wavelengths of 375 and 250 nanometers will appear at exactly the same angle. There must be some auxiliary dispersion or filtering to separate these orders if overlapping is to be avoided. Usually combinations of transmission filters (input filtering) and photographic emulsion (output filtering) are used to properly separate overlapping orders. Another technique is a use of a prism predisperser to select the spectral wavelength range of
interest.

4.4 Output Measurement

There are many output measurement techniques available to determine the output emission of a spectrometer. The major point to be made in this area is that the output to be measured is a function of the diffraction grating efficiency (which is a function of wavelength). To complicate the matter, the measurement device (eye, photodiode, photomultiplier tube, photographic film, etc.) also has a sensitivity which is a function of wavelength. Therefore, extreme care must be taken when comparing measured or observed relative values of spectral emission, especially when there is a large difference in wavelength.
CHAPTER 5

EXPERIMENTAL MEASUREMENTS

5.1 General Information

The experimental measurements cover two areas. The first is the pulse mode operation measurement of values of transient thermal resistance of an infrared emitting diode. Measurements will be taken for different values of pulse width and duty cycle. The second is to compare transient thermal resistance predicted values of peak emission wavelength change against measured values.

5.2 Transient Thermal Resistance Measurements

The infrared emitting diode selected for transient thermal resistance measurements was the Monsanto ME 7140 type because it is typical of a wide variety of other devices.

The first measurement procedure was to obtain the forward voltage versus temperature curve for a constant forward current, in this case 10 milliamperes. The purpose was to provide a baseline to determine the actual junction temperature of the infrared emitting diode at the end of a current pulse. The basic calibration circuit is shown in Figure 9. The oven temperature was measured using a copper-constantan thermocouple and a digital
Fig. 9  Forward voltage versus junction temperature calibration circuit

temperature indicator. A digital voltmeter was used to measure the forward voltage of the diode and a laboratory type milliammeter was used to measure the diode forward current. The resistor $R_L$ is for overload current protection while $R_V$ is used to maintain the 10 milliampere forward current.

As expected, the resulting data showed the variation in forward voltage over a temperature range from 25°C to 75°C to vary linearly with temperature. The measured forward voltage temperature coefficient was $-1.76 \text{ mv/°C}$ as compared to the manufacturers stated value of $-1.8 \text{ mv/°C}$. 

Having defined a baseline to measure the junction temperature at the end of a current pulse, the next step was to build a measurement circuit to obtain data to calculate values of transient thermal resistance. This
circuit is presented in Figure 10. A continuous forward current of 10 milliamperes is passed through the diode when the transistor is turned off. This enables the

![Diode Circuit Diagram]

**Fig. 10 Transient thermal resistance data measurement circuit**

determination of the junction temperature by measuring the forward voltage across the diode and finding the corresponding temperature on the calibration graph. During the application of a current pulse through the transistor driver circuit, the junction temperature rises to a value dependent on the transient thermal resistance of the diode. If we place an oscilloscope across the diode, we can measure the forward voltage immediately after the input pulse goes to zero and obtain the junction temperature at the end of the applied pulse. This approach was not used, however, because of the small
variation in forward voltage observed during the measurement process. Instead, a measurement was made of the change in forward voltage at the end of a current pulse with respect to the ambient (no pulse input) forward voltage. A plot of these measurements is presented in Figure 11, and represents the application of a 7.58 watt power pulse. The rise at the end of the curve is due to the fact that the junction temperature did not return to ambient temperature prior to the application of the next pulse. Pulse current was measured by interchanging the diode and \( R_R \), a one ohm resistor, and measuring the voltage drop across the resistor.

\[
\begin{align*}
\text{FORWARD VOLTAGE CHANGE (\text{mV})} \\
\text{PULSE WIDTH (MICROSECONDS)}
\end{align*}
\]

\[
\begin{align*}
P_D &= 7.58 \text{ W} \\
C &= 5 \text{ MS}
\end{align*}
\]

Fig. 11 Forward voltage variation as a function of pulse width

The value of \( \theta_I(t) \) was calculated using equation 3.1
with \( \Theta_{JA}(t) \) substituted for \( \Theta_{JR} \) and \( T_A \) substituted for \( T_R \). The value of \( T_J - T_A \) was determined by dividing the measured voltage contained in Figure 11 by 1.76 millivolts. A summary of the calculated values of \( \Theta_{JA}(t) \) are presented in Table 5-1, for various pulse conditions.

Table 5-1. Summary of Results

<table>
<thead>
<tr>
<th>Pulse Width (microseconds)</th>
<th>Duty Cycle</th>
<th>( \Theta_{JA}(t) ) °C/W</th>
</tr>
</thead>
<tbody>
<tr>
<td>50</td>
<td>.01</td>
<td>1.87</td>
</tr>
<tr>
<td>100</td>
<td>.02</td>
<td>2.99</td>
</tr>
<tr>
<td>150</td>
<td>.03</td>
<td>4.49</td>
</tr>
<tr>
<td>200</td>
<td>.04</td>
<td>5.62</td>
</tr>
<tr>
<td>250</td>
<td>.05</td>
<td>6.37</td>
</tr>
<tr>
<td>300</td>
<td>.06</td>
<td>7.49</td>
</tr>
<tr>
<td>350</td>
<td>.07</td>
<td>8.99</td>
</tr>
<tr>
<td>400</td>
<td>.08</td>
<td>10.11</td>
</tr>
<tr>
<td>450</td>
<td>.09</td>
<td>11.99</td>
</tr>
<tr>
<td>500</td>
<td>.10</td>
<td>13.11</td>
</tr>
</tbody>
</table>

5.3 Wavelength Measurements

The first procedure was to check the spectrometer to insure that all components were properly mounted and that the various image planes were properly centered. Some small adjustments were required and were accomplished in accordance with the information contained in the instruction manual.

The next step was to calibrate the measurement
instrument. This was accomplished by using a low pressure mercury lamp and its associated 546.07 nanometer visible line image at the spectrometer wavelength settings of 546.07 and 1,092.15 nanometers and moving the focusing mirror and grating holder adjustments in accordance with the information contained in the instruction manual.

The peak emission wavelength change of some light and infrared emitting diodes were measured as a function of forward current in the continuous mode of operation. The output of the spectrometer was measured with an optical power meter since the photomultiplier tubes available for use with the spectrometer were not responsive in the 940 nanometer region of the spectrum. The observed results were in good agreement with the values predicted by using the manufacturers stated values of thermal resistance, $\Theta_{JA}$, and the wavelength temperature coefficient (case temperature). The input optical system design described in Chapter 4 was used as a basis to couple the source to the spectrometer and produced very good results.

The concept to measure the wavelength shift for pulse mode operation of infrared emitting diodes was to observe and record the maximum voltage output from a photomultiplier tube or photodiode detection circuit and plot the information on a graph. The expected results are illustrated in Figure 12 with the change in wavelength.
Fig. 12 Plot of maximum detector output versus wavelength for a given pulse power, duration and repetition period during the application of a pulse, $\Delta \lambda$, being estimated from the graph.

An attempt was made to build a photodiode detector and to use an existing one, both without success. Based on this and the non-availability of any other infrared detection equipment for pulse mode operation, no experimental measurements were taken to compare transient thermal resistance predicted values of peak emission wavelength change against measured values.
CHAPTER 6

CONCLUSION

6.1 Discussion

The research effort has shown that the use of transient thermal resistance is an applicable technique to describe the temperature behavior of an infrared emitting diode junction when the device is operated in the pulse mode. This being the case, we can also use this data to determine the peak emission wavelength change of the diode for pulse mode operation. It is felt that with an appropriate infrared detector, the above would have been demonstrated by experimental measurement.

In summary, the research effort has been very interesting and has proved itself beneficial in work related projects.

6.2 Application of Research Effort

A potential application for the use of infrared emitting diodes based on the knowledge gained from this research effort is for a remote temperature sensing system. While the idea has not been investigated to any great detail, it appears to have some practical uses.

The general concept is to make use of the diode's change in emission wavelength as a function of temperature.
By operating the device in the pulse mode to increase output power and coupling the diode to a suitable detector, say by means of an optical fiber, we could monitor the wavelength and determine the remote temperature. A means to monitor the wavelength could be by the use of narrow band optical filters.

6.3 Recommendations

The Hilger-Engis Model 1000 Monochromator Spectrometer is an excellent device with which to perform optical measurements. To improve its usefulness, it is recommended that the following accessories be purchased:

(a) Photomultiplier tube and attachment for near infrared measurements

(b) Accessory bar

(c) Bar carriages

(d) Focusable eyepiece
LIST OF REFERENCES


5. The Optoelectronics Data Book for Design Engineers. Dallas: Texas Instruments Inc., 1975
